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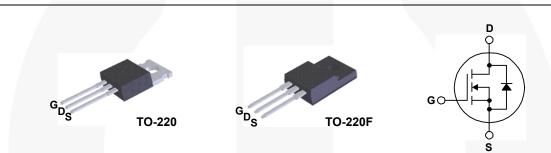
FQP13N50C / FQPF13N50C N-Channel QFET[®] MOSFET 500 V, 13 A, 480 mΩ

Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction, electronic lamp ballasts based on half bridge topology.

Features

- 13 A, 500 V, $R_{DS(on)}$ = 480 m Ω (Max.) @ V_{GS} = 10 V, I_D = 6.5 A
- Low Gate Charge (Typ. 43 nC)
- Low Crss (Typ. 20 pF)
- 100% Avalanche Tested



Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

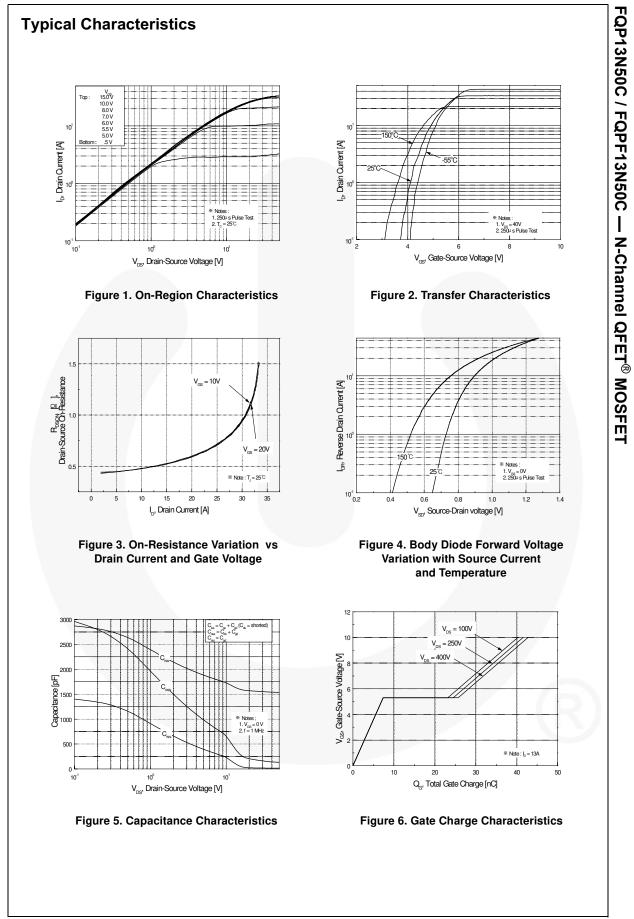
Symbol	Parameter		FQP13N50C FQPF13N50C		Units
V _{DSS}	Drain-Source Voltage		5	00	V
I _D	Drain Current - Continuous (T _C = 25°C	;)	13	13 *	А
	- Continuous (T _C = 100°	C)	8	8 *	А
I _{DM}	Drain Current - Pulsed	(Note 1)	52	52 *	А
V _{GSS}	Gate-Source Voltage		± 30		V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	8	860	
I _{AR}	Avalanche Current	(Note 1)		13	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	1	9.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4	.5	V/ns
PD	Power Dissipation ($T_C = 25^{\circ}C$)		195	48	W
	- Derate above 25°C		1.56	0.39	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
Τ _L	Maximum lead temperature for soldering purposes,		300		°C
	1/8" from case for 5 seconds				

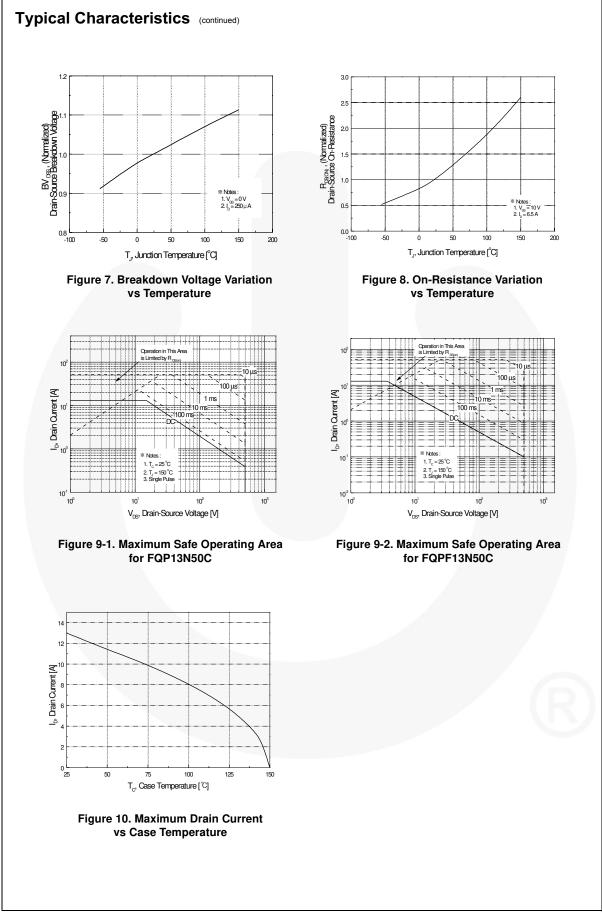
* Drain current limited by maximum junction temperature

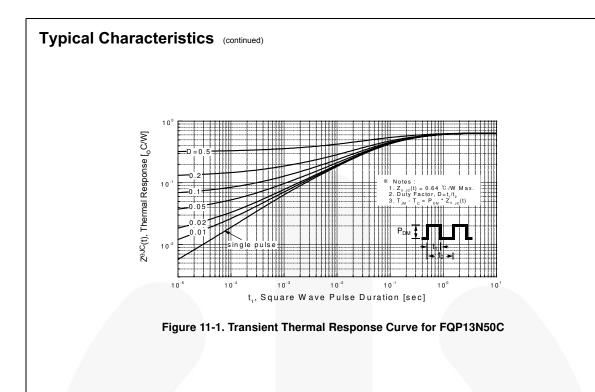
Thermal Characteristics

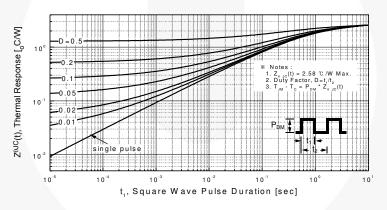
Symbol	Parameter	FQP13N50C	FQPF13N50C	Units	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.64	2.58	°C/W	
$R_{ extsf{ heta}JS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5		°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W	

FQP13N50C_F105 FQP13N50C TO-		· ·	Package		Packing Method Reel Tube N/		Tape Width N/A		Quantity	
			TO-220						50 units	
		TO-220F	220F Tube N/			N/A		50 units		
	cal Cha		= 25°C unless o				T		11-14	
Symbol		Parameter		Test Condition	S	Min	Тур	Max	Unit	
	racteristi					1	T	1	1	
BV _{DSS}	Drain-Sour	ce Breakdown Volta	ge V _C	V_{GS} = 0 V, I _D = 250 µA					V	
ΔBV _{DSS} / ΔT _J	Breakdowr Coefficient	n Voltage Temperatu	D,	I_D = 250 µA, Referenced to 25°C			0.5		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current		nt	V _{DS} = 500 V, V _{GS} = 0 V				1	μA	
				$V_{DS} = 400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$				10	μΑ	
IGSSF	-	Leakage Current, F		$V_{GS} = 30 V, V_{DS} = 0 V$				100	nA	
IGSSR	Gate-Body	Leakage Current, R	everse v _e	_{SS} = -30 V, V _{DS} = 0 V				-100	nA	
On Cha	racteristi	cs								
V _{GS(th)}	Gate Three	shold Voltage	V	$_{0S} = V_{GS}, I_{D} = 250 \ \mu A$		2.0		4.0	V	
R _{DS(on)}	Static Drain On-Resista			_{GS} = 10 V, I _D = 6.5 A			0.39	0.48	Ω	
9 _{FS}	Forward Tr	ansconductance	VC	_{os} = 40 V, I _D = 6.5 A			15		S	
C _{iss}	ic Charac Input Capa		V	_{os} = 25 V, V _{GS} = 0 V,			1580	2055	pF	
C _{oss}	Output Cap	pacitance		1.0 MHz			180	235	pF	
C _{rss}	Reverse T	ansfer Capacitance					20	25	pF	
Switchi	ng Chara	cteristics								
t _{d(on)}	Turn-On D		V	V _{DD} = 250 V, I _D = 13 A,			25	60	ns	
t _r	Turn-On R	ise Time		$_{\Omega} = 250 \text{ V}, \text{ ID} = 13 \text{ A},$ $_{\Omega} = 25 \Omega$			100	210	ns	
t _{d(off)}	Turn-Off D	elay Time		, 2011			130	270	ns	
t _f	Turn-Off Fa	all Time			(Note 4)		100	210	ns	
Qg	Total Gate	Charge	Vr	_{os} = 400 V, I _D = 13 A,			43	56	nC	
Q _{gs}	Gate-Sour	ce Charge		_{SS} = 10 V			7.5		nC	
Q _{gd}	Gate-Drain	Charge					18.5		nC	
Drain-S	ource Die	ode Characteris	tics and I	Maximum Rating	s					
I _S	Maximum	aximum Continuous Drain-Source Diode Forward Current					13	А		
I _{SM}	Maximum	Pulsed Drain-Source	Diode Forw	Forward Current				52	Α	
V _{SD}	Drain-Sour	ce Diode Forward V	oltage V _G	V _{GS} = 0 V, I _S = 13 A				1.4	V	
t _{rr}	Reverse R	ecovery Time	Ve	V _{GS} = 0 V, I _S = 13 A,			410		ns	
Q _{rr}	Reverse R	ecovery Charge	dl _F	dI _F / dt = 100 A/µs			4.5		μC	
lotes: . Repetitive ra	ating : pulse-widt _{.s} = 13 A, V _{DD} = {	h limited by maximum junc					I	I	C	

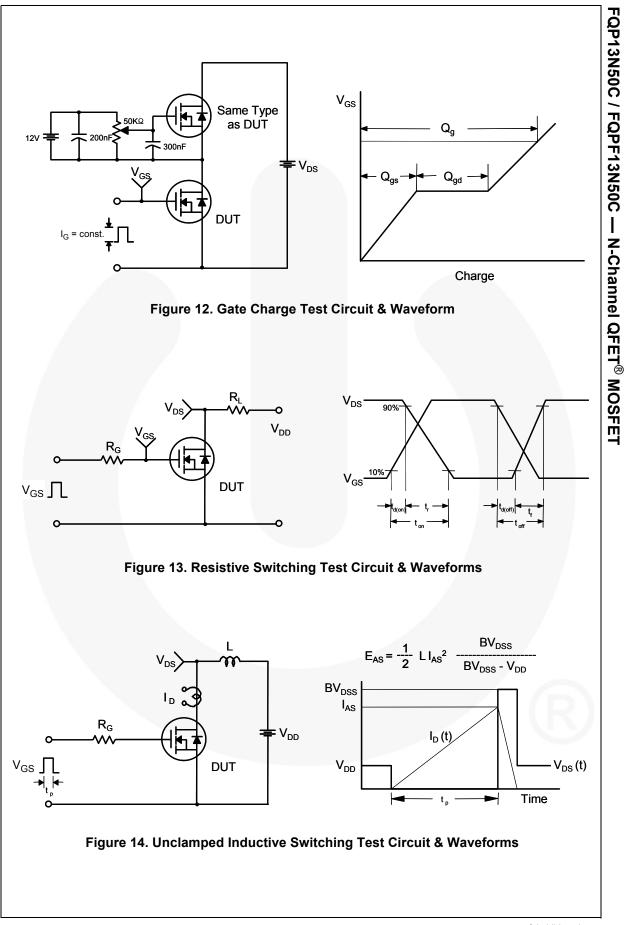


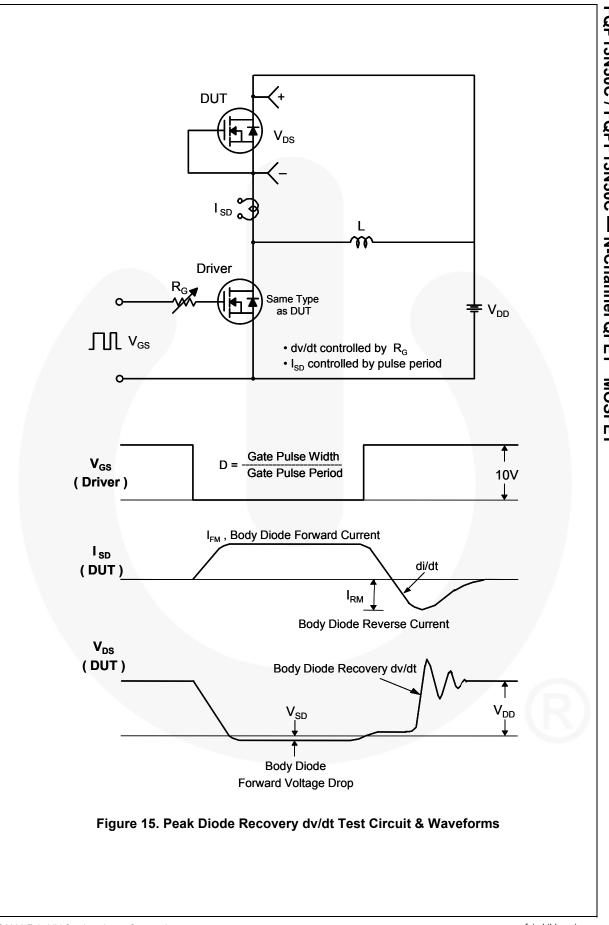


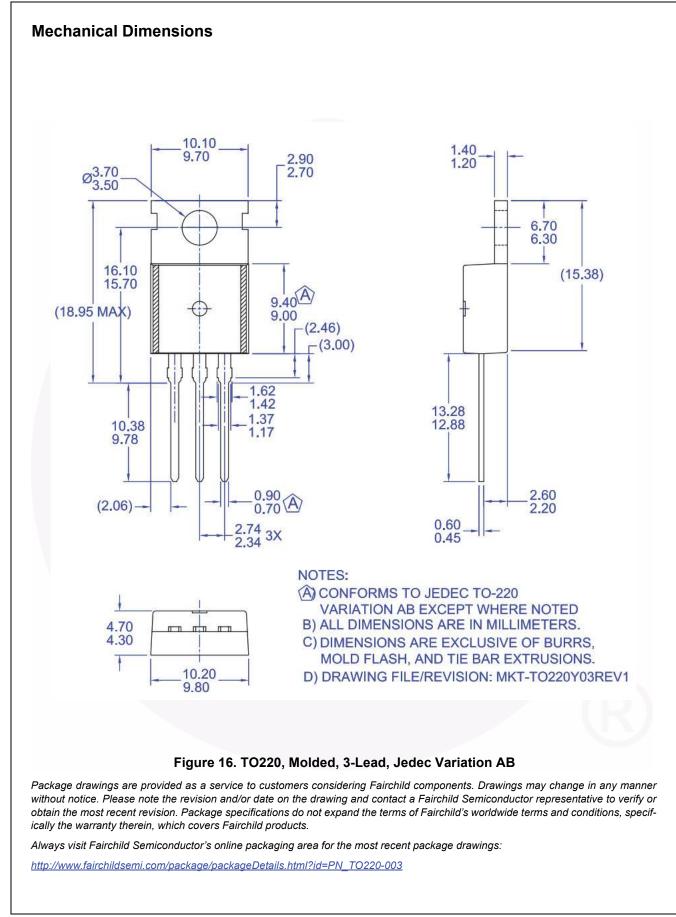


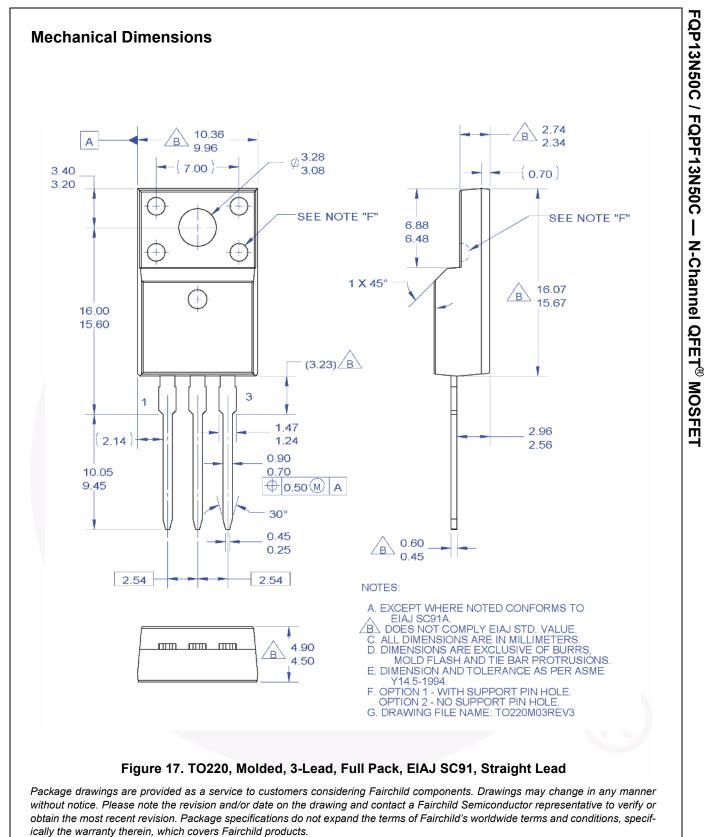












Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TF220-003



Obsolete

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild

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